

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Complete if Known Application Number Unknown <u>10/788,810</u> Filing Date Even Date Herewith <u>2-27-04</u> First Named Inventor Forbes, Leonard Group Art Unit Unknown <u>2825</u> Examiner Name Unknown <u>Anya</u>				
Sheet 1 of 5		Attorney Docket No: 1303.027US2				

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		<small>Complete if Known</small>				
		Application Number	Unknown <i>10/88,810</i>			
		Filing Date	Even Date Herewith <i>2-27-04</i>			
		First Named Inventor	Forbes, Leonard			
		Group Art Unit	Unknown <i>2825</i>			
		Examiner Name	Unknown <i>Amy C</i>			
Sheet 2 of 5		Attorney Docket No: 1303.027US2				

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EXAMINER	<i>Anita G</i>	DATE CONSIDERED	<i>8/4/04</i>
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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional) ² Applicant is to place a check mark here if English language Translation is attached

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		Filing Date	Even Date Herewith <i>2-27-04</i>
		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown <i>2825</i>
		Examiner Name	Unknown <i>Anuj</i>
Sheet 3 of 5		Attorney Docket No: 1303.027US2	

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		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown <i>2825</i>
		Examiner Name	Unknown <i>Amy a</i>
Sheet 4 of 5		Attorney Docket No: 1303.027US2	

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PTO/SB/04A (10-01)

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		First Named Inventor	Forbes, Leonard
		Group Art Unit	Unknown <i>2820</i>
		Examiner Name	Unknown <i>Any</i>
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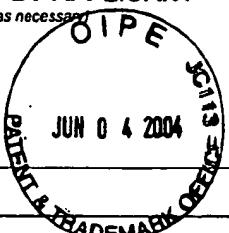
A. Anderson

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Substitute Disclosure Statement Form (PTO-1449)

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>		Application Number	10/788810
 JUN 04 2004		Filing Date	February 27, 2004
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2812 2828
		Examiner Name	Unknown Amy g
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